National Semiconductor

April 1994

54ACTQ/74ACTQ14
Quiet Series Hex Inverter with Schmitt Trigger Input

General Description

The 'ACTQ14 contains six inverter gates each with a Schmitt trigger input. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals. In addition, they have a greater noise margin than conventional inverters.

The 'ACTQ14 utilizes NSC Quiet Series Technology to guarantee quiet output switching and improve dynamic threshold performance. FACT Quiet Series™ features GTO™ output control and undershoot corrector in addition to a split ground bus for superior performance.

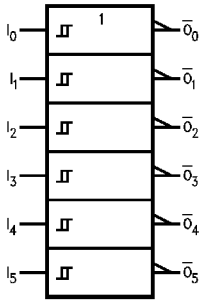
The 'ACTQ14 has hysteresis between the positive-going and negative-going input thresholds (typically 1.0V) which is determined internally by transistor ratios and is essentially insensitive to temperature and supply voltage variations.

Features

- I_{CC} reduced by 50%
- Guaranteed simultaneous switching noise level and dynamic threshold performance
- Improved latch-up immunity
- 4 kV minimum ESD performance
- Guaranteed pin-to-pin skew AC performance
- Outputs source/sink 24 mA
- Standard Military Drawing (SMD)
  — 'ACTQ14: 5962-92183

Logic Symbol

IEEE/IEC



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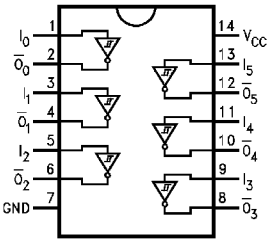
Connection Diagrams

Pin Assignment for DIP, Flatpak and SOIC



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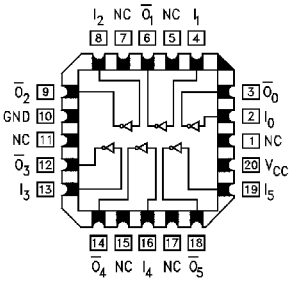
Pin Assignment for LCC



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Function Table

Input	Output
A	$\overline{O}$
L	H
H	L

Pin Names	Description
I_n	Inputs
$\overline{O}_n$	Outputs

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Absolute Maximum Rating (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5V to +7.0V
DC Input Diode Current (I_{IK})	
V_I = −0.5V	−20 mA
V_I = V_{CC} + 0.5V	+20 mA
DC Input Voltage (V_I)	−0.5V to V_{CC} + 0.5V
DC Output Diode Current (I_{OK})	
V_O = −0.5V	−20 mA
V_O = V_{CC} + 0.5V	+20 mA
DC Output Voltage (V_O)	−0.5V to V_{CC} + 0.5V
DC Output Source or Sink Current (I_O)	±50 mA
DC V_{CC} or Ground Current per Output Pin (I_{CC} or I_{GND})	±50 mA
Storage Temperature (T_{STG})	−65°C to +150°C
DC Latch-Up Source or Sink Current	±300 mA
Junction Temperature (T_J)	
CDIP	175°C
PDIP	140°C

Note 1: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation outside of databook specifications.

Recommended Operating Conditions (Note 2)

Supply Voltage (V_{CC})	
'ACTQ	4.5V to 5.5V
Input Voltage (V_I)	0V to V_{CC}
Output Voltage (V_O)	0V to V_{CC}
Operating Temperature (T_A)	
74ACTQ	−40°C to +85°C
54ACTQ	−55°C to +125°C

Note 2: All commercial packaging is not recommended for applications requiring greater than 2000 temperature cycles from −40°C to +125°C.

DC Characteristics for 'ACTQ Family Devices

Symbol	Parameter	V_{CC} (V)	74ACTQ T_A = +25°C	54ACTQ T_A = −55°C to +125°C	74ACTQ T_A = −40°C to +85°C	Units	Conditions
			Typ	Guaranteed Limits			
V_{IH}	Minimum High Level Input Voltage	4.5	1.5	2.0	2.0	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		5.5	1.5	2.0	2.0		
V_{IL}	Maximum Low Level Input Voltage	4.5	1.5	0.8	0.8	V	V_{OUT} = 0.1V or V_{CC} − 0.1V
		5.5	1.5	0.8	0.8		
V_{OH}	Minimum High Level Output Voltage	4.5	4.49	4.4	4.4	V	I_{OUT} = −50 μA
		5.5	5.49	5.4	5.4		
		4.5		3.86	3.70	3.76	V	*V_{IN} = V_{IL} or V_{IH} I_{OH} −24 mA
		5.5		4.86	4.70	4.76		
V_{OL}	Maximum Low Level Output Voltage	4.5	0.001	0.1	0.1	V	I_{OUT} = 50 μA
		5.5	0.001	0.1	0.1		
		4.5		0.36	0.50	0.44	V	*V_{IN} = V_{IL} or V_{IH} I_{OL} 24 mA
		5.5		0.36	0.50	0.44		
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	±1.0	μA	V_I = V_{CC}, GND
$V_{h(max)}$	Maximum Hysteresis	4.5		1.4	1.4	1.4	V	T_A = Worst Case
		5.5		1.6	1.6	1.6		

*All outputs loaded; thresholds on input associated with output under test.

DC Characteristics for 'ACTQ Family Devices (Continued)

Symbol	Parameter	V_{CC} (V)	74ACTQ $T_A = +25°C$	54ACTQ $T_A = -55°C$ to $+125°C$	74ACTQ $T_A = -40°C$ to $+85°C$	Units	Conditions
			Typ	Guaranteed Limits			
$V_{h(min)}$	Minimum Hysteresis	4.5 5.5		0.4 0.5	0.4 0.5	0.4 0.5	V	T_A = Worst Case
V_t^+	Maximum Positive Threshold	4.5 5.5		2.0 2.0	2.0 2.0	2.0 2.0	V	T_A = Worst Case
V_t^-	Minimum Negative Threshold	4.5 5.5		0.8 0.8	0.8 0.8	0.8 0.8	V	T_A = Worst Case
I_{CCT}	Maximum I_{CC}/Input	5.5	0.6		1.6	1.5	mA	$V_I = V_{CC} - 2.1V$
I_{OLD}	†Minimum Dynamic Output Current	5.5			50	75	mA	V_{OLD} = 1.65V Max
I_{OHD}		5.5			−50	−75	mA	V_{OHD} = 3.85V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		2.0	40.0	20.0	μA	$V_{IN} = V_{CC}$ or GND (Note 1)
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	5.0	1.1	1.5			V	*Figures 12, 13* (Notes 2, 3)
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	5.0	−0.6	−1.2			V	*Figures 12, 13* (Notes 2, 3)
V_{IHD}	Minimum High Level Dynamic Input Voltage	5.0	1.9	2.2			V	(Notes 2, 4)
V_{ILD}	Maximum Low Level Dynamic Input Voltage	5.0	1.2	0.8			V	(Notes 2, 4)

†Maximum test duration 2.0 ms, one output loaded at a time.

Note 1: I_{CC} for 54ACTQ @ 25°C is identical to 74ACTQ @ 25°C.

Note 2: Plastic DIP package.

Note 3: Max number of outputs defined as (n). Data inputs are 0V to 3V. One output @ GND.

Note 4: Max number of data inputs (n) switching. (n−1) inputs switching 0V to 3V ('ACTQ). Input-under-test switching: 3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f = 1 MHz.

AC Electrical Characteristics

Symbol	Parameter	V_{CC}* (V)	74ACTQ $T_A = +25°C$, $C_L = 50$ pF			54ACTQ $T_A = -55°C$ to $+125°C$, $C_L = 50$ pF		74ACTQ $T_A = -40°C$ to $+85°C$, $C_L = 50$ pF		Units
			Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}	Propagation Delay Data to Output	5.0	3.0	8.0	10.0	1.5	10.0	3.0	11.0	ns
t_{PHL}	Propagation Delay Data to Output	5.0	3.0	8.0	10.0	1.5	9.5	3.0	11.0	ns
t_{OSHL}, t_{OSLH}	Output to Output Skew**	5.0		0.5	1.0		1.0		1.0	ns

*Voltage Range 5.0 is 5.0V ±0.5V.

**Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}). Parameter guaranteed by design.

Capacitance

Symbol	Parameter	Typ	Units	Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = OPEN
C_{PD}	Power Dissipation Capacitance	80	pF	V_{CC} = 5.0V

FACT Noise Characteristics

The setup of a noise characteristics measurement is critical to the accuracy and repeatability of the tests. The following is a brief description of the setup used to measure the noise characteristics of FACT.

Equipment:

Hewlett Packard Model 8180A Word Generator
PC-163A Test Fixture
Tektronics Model 7854 Oscilloscope

Procedure:

1. Verify Test Fixture Loading: Standard Load 50 pF, 500Ω.
2. Deskew the word generator so that no two channels have greater than 150 ps skew between them. This requires that the oscilloscope be deskewed first. Swap out the channels that have more than 150 ps of skew until all channels being used are within 150 ps. It is important to deskew the word generator channels before testing. This will ensure that the outputs switch simultaneously.
3. Terminate all inputs and outputs to ensure proper loading of the outputs and that the input levels are at the correct voltage.
4. Set V_{CC} to 5.0V.
5. Set the word generator to toggle all but one output at a frequency of 1 MHz. Greater frequencies will increase DUT heating and affect the results of the measurement.

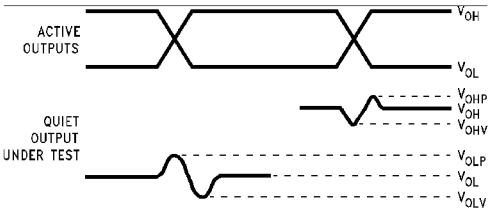

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FIGURE 1. Quiet Output Noise Voltage Waveforms

Note A. V_{OHV} and V_{OLP} are measured with respect to ground reference.

Note B. Input pulses have the following characteristics: f = 1 MHz, t_r = 3 ns, t_f = 3 ns, skew < 150 ps.

6. Set the word generator input levels at 0V LOW and 3V HIGH for ACT devices and 0V LOW and 5V HIGH for AC devices. Verify levels with a digital volt meter.

FACT Noise Characteristics (Continued)

V_{OLP}/V_{OLV} and V_{OHP}/V_{OHV}:

- Determine the quiet output pin that demonstrates the greatest noise levels. The worst case pin will usually be the furthest from the ground pin. Monitor the output voltages using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- Measure V_{OLP} and V_{OLV} on the quiet output during the HL transition. Measure V_{OHP} and V_{OHV} on the quiet output during the LH transition.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

V_{ILD} and V_{IHD}:

- Monitor one of the switching outputs using a 50Ω coaxial cable plugged into a standard SMB type connector on the test fixture. Do not use an active FET probe.
- First increase the input LOW voltage level, V_{IL}, until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input LOW voltage level at which oscillation occurs is defined as V_{ILD}.
- Next increase the input HIGH voltage level on the word generator, V_{IH} until the output begins to oscillate. Oscillation is defined as noise on the output LOW level that exceeds V_{IL} limits, or on output HIGH levels that exceed V_{IH} limits. The input HIGH voltage level at which oscillation occurs is defined as V_{IHD}.
- Verify that the GND reference recorded on the oscilloscope has not drifted to ensure the accuracy and repeatability of the measurements.

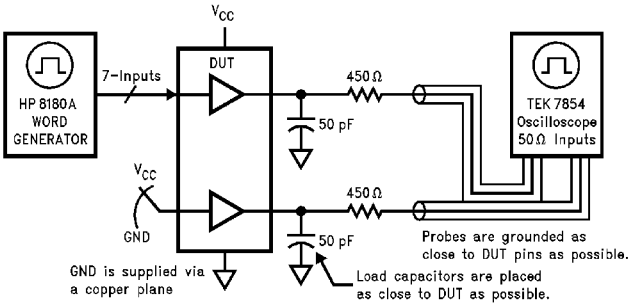

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FIGURE 2. Simultaneous Switching Test Circuit

Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

74ACTQ 14 P C QR

Temperature Range Family
74ACTQ = Commercial TTL—Compatible
54ACTQ = Military TTL—Compatible

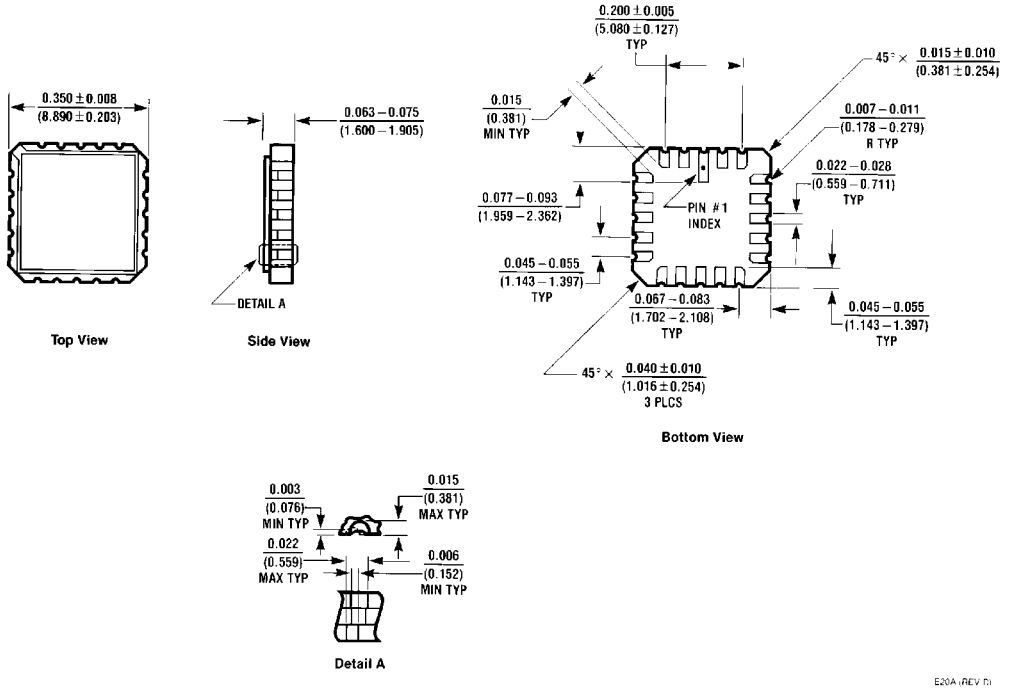
Device Type

Package Code
P = Plastic DIP
D = Ceramic DIP
F = Flatpak
L = Leadless Ceramic Chip Carrier (LCC)
S = Small Outline (SOIC)

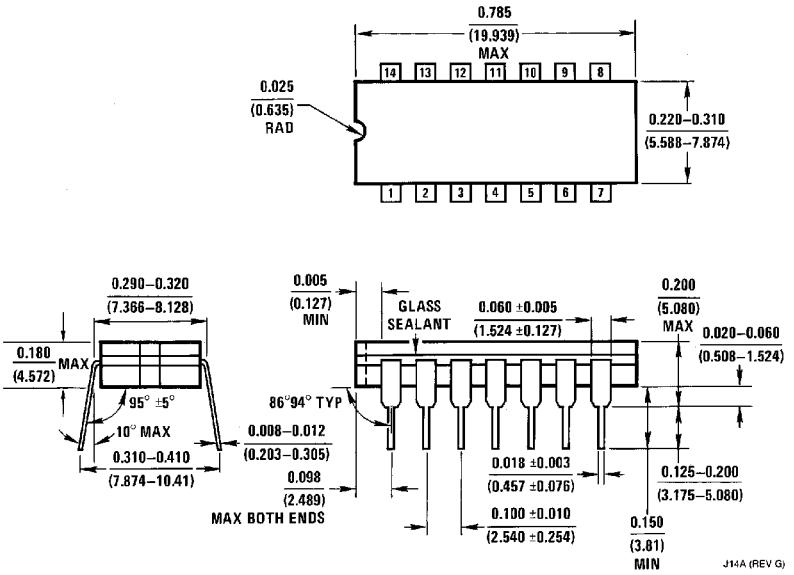
Temperature Range
C = Commercial (−40°C to +85°C)
M = Military (−55°C to +125°C)

Special Variations
X = Devices shipped in 13″ reels
QR = Commercial grade device with burn-in
QB = Military grade device with environmental and burn-in processing shipped in tubes

Physical Dimensions inches (millimeters)

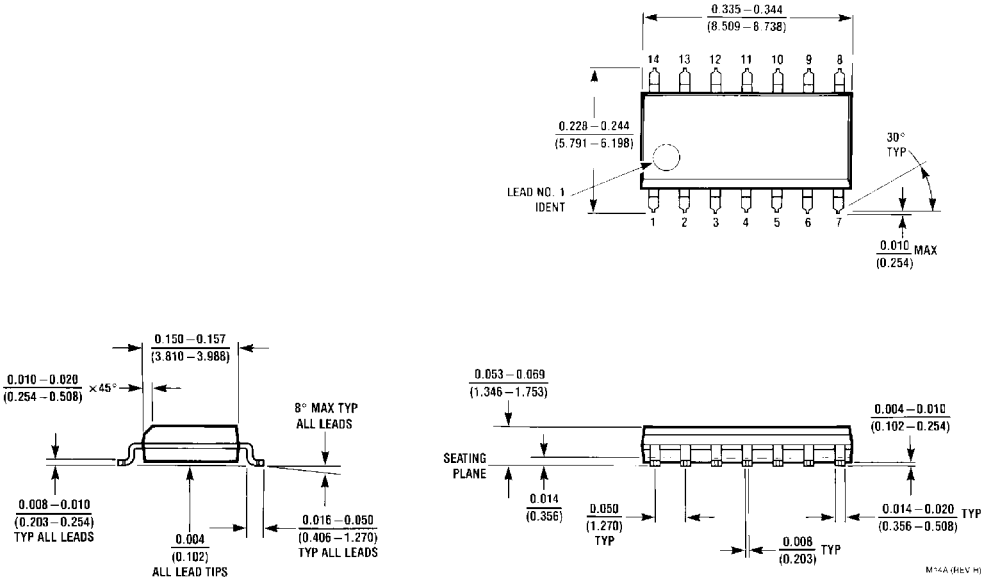


20-Terminal Ceramic Leadless Chip Carrier (L)
NS Package Number E20A

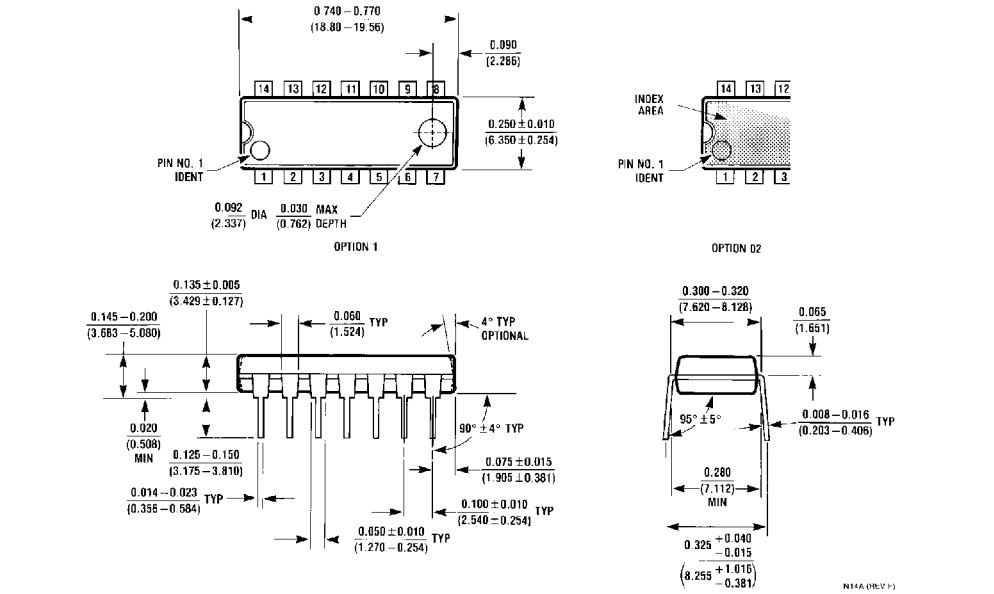


14-Lead Ceramic Dual-In-Line Package (D)
NS Package Number J14A

Physical Dimensions inches (millimeters) (Continued)

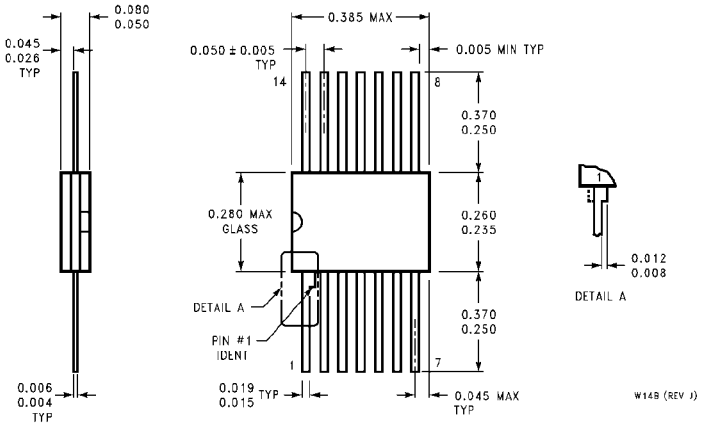


14-Lead Small Outline Integrated Circuit (S)
NS Package Number M14A



14-Lead Plastic Dual-In-Line Package (P)
NS Package Number N14A

Physical Dimensions inches (millimeters) (Continued)



14-Lead Ceramic Flatpak (F)
NS Package Number W14B

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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